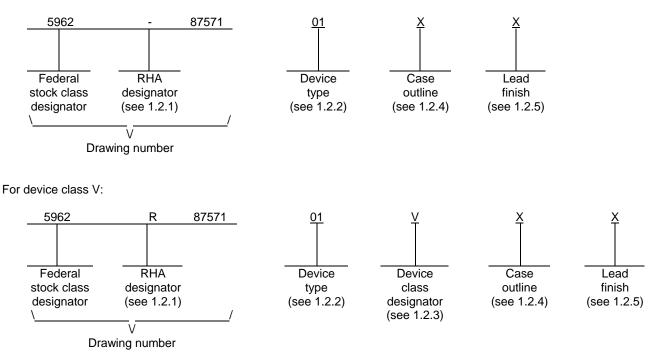
LTR	DESCRIPTION							DATE (YR-MO-DA)		APPROVED								
А	Changes IAW NOR 5962-R036-93.							92-12-23		M. A. Frye								
В	Change boiler	Change boilerplate to add one-part numbers. Add table IIB for delta limits. Editorial changes throughout. Redrawn							97-03-07		R. Monnin							
С	Add radiation I	ardness as	ssuranc	e requi	iremen	ts. Up	date bo	oilerplat	errp			98-0	6-18			R. Mo	onnin	
D	Changes to 1.	, table IIB,	and 4.	4.4.1. •	-rrp							99-0	4-12			R. Mo	onnin	
Е	Changes to tal	le IIA footr	notes a	nd table	e IIB	-rrp						00-0	9-15			R. M	onnin	
F	Add device typ table I. Update			radiatio	on value	e for the	e ambie	ent erro	r test ir	١		02-0	5-24			R. N	lonnin	
G	Add paragraph	4.4.4.1. E	ditorial	change	es thro	ughout	rrp					07-0	5-14		F	Robert	M. Heb	er
THE ORIGINA REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A	L FIRST PAGE O	REV SHE	/) BY	G 1	G 2	CED.	G 4	G 5	G 6	G 7	G 8	G 9	G 10	G 11	G 12	G 13	G 14
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DRAWI FOR L		REV SHE PRE M CHE CHE	/ EET) BY 3. Kelle BY Cenzo D BY	G 1 ther	G	G	4 MIC HAI	5 DI ROC	6 EFEN CC CIRCU	7 SE SI DLUM http JIT, L TWC	8 IBUS, p://ww LINE/) TEF	9 , OHI , OHI , w.ds AR, F	10 NTER D 432 cc.dla cc.dla RADIA AL TI	11 218-33 a.mil	12 .UMB 990	13	14
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DRA THIS DRAWIL FOR L DEPA	NDARD DCIRCUIT AWING NG IS AVAILABL JSE BY ALL	REV SHE PRE CHE CHE	/ EET PARED Aarcia E CKED D. A. Did PROVEI Nelson) BY 3. Kelle BY Cenzo D BY Hauck	G 1 her	G 2	G	4 MIC HAI	5 DI ROC	6 EFEN CC CIRCU	7 SE SI DLUM http JIT, L TWC	8 IBUS, p://ww LINE/) TEF	9 , OHI , OHI , w.ds AR, F	10 NTER D 432 cc.dla	11 218-33 a.mil	12 .UMB 990	13 US	14
REV SHEET REV SHEET REV STATUS OF SHEETS PMIC N/A STA MICRO DRA THIS DRAWI FOR L DEPA	NDARD DCIRCUIT AWING NG IS AVAILABLI JSE BY ALL ARTMENTS NCIES OF THE	REV SHE PRE CHE CHE	/ EET PARED Aarcia E CKED D. A. Did PROVEI Nelson) BY 3. Kelle BY Cenzo D BY Hauck APPRC 37-09-2 LEVEL	G 1 ther	G 2	G	4 MIC HAI TRA	5 DI ROC	6 EFEN CC CIRCU NED, DUCE	7 SE SI DLUM http JIT, L TWC	8 IBUS, D://ww LINE/ D TEF	9 , OHI , OHI , w.ds AR, F	10 NTER D 432 cc.dla RADIA AL TI	11 218-39 a.mil	12 .UMB 990	US	14

1. SCOPE

1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following examples.

For device classes M and Q:



1.2.1 <u>RHA designator</u>. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	AD590J	Temperature transducer
02	AD590K	Temperature transducer
03	AD590L	Temperature transducer
04	AD590M	Temperature transducer

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as listed below. Since the device class designator has been added after the original issuance of this drawing, device classes M and Q designators will not be included in the PIN and will not be marked on the device.

Device class	Device requirements documentation							
Μ	Vendor self-certification to the requirements for MIL-STD-883 compliant, non- JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A							
Q or V	Certification and qualification to MIL-PRF-38535							
STANDARD MICROCIRCUIT DRAWIN	G	SIZE A		5962-87571				
DEFENSE SUPPLY CENTER COLU COLUMBUS, OHIO 43218-399	UMBUS REVISION LEVEL SHEET							
C FORM 2224			1	1				

1.2.4 <u>Case outline(s)</u> . Th	e case outline(s) are a	as designated	in MIL-STD-1835	and as follo	WS:			
Outline letter	Descriptive designate	or <u>Term</u>	inals	Package	<u>e style</u>			
X Y	See figure 1 See figure 1	2	<u>2</u> 3	Flat pac Metal ca				
1.2.5 <u>Lead finish</u> . The lea appendix A for device class		d in MIL-PRF-	38535 for device of	classes Q ar	nd V or MIL-PR	F-38535,		
1.3 Absolute maximum ra	a <u>tings</u> . <u>1</u> /							
Forward voltage (E+ to E-)								
÷ .	Case to E+ or E-)							
Storage performance	temperature range			-65°C to +				
Lead temperature ran Thermal resistance (6	nge (soldering, 10 seco _{JA}):	onds)		+300°C				
MEDIUM	θ_{JC} + θ_{CA} (°C/V	N)		T _S <u>3</u> /				
	Y <u>4</u> /	X <u>4</u> /	Ň	Y <u>4</u> /	X <u>4</u> /			
Aluminum block Stirred oil <u>5</u> /	30 42	10 60		0.6 1.4	0.1 0.6			
Moving air <u>6</u> /		00			0.0			
With heat sink Without heat sink Still air	45 115	 190		5.0 13.5	 10.0			
With heat sink Without heat sink	191 480	 650		108 60	 30			
1.4 Recommended opera	ating conditions.							
	(V _{CC}) mperature range							
1.5 Radiation features.								
	available (dose rate =			100 Krads((Si) <u>7</u> /			
2. APPLICABLE DOCUM	IENTS							
2.1 <u>Government specifica</u> of this drawing to the extent solicitation or contract.								
 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability. 2/ Device types 02, 03, and 04 class V rated performance temperature range = -55°C to +125°C. 3/ The time constant is defined as the time required to reach 63.2 percent of an instantaneous temperature change. 4/ Y - 3-pin can; X - 2-pin flat package. 5/ T is dependent upon velocity of oil: average of several velocities listed above. 6/ Air velocity = 9 feet per second. 7/ These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A. 								
MICROCIR	NDARD CUIT DRAWING Y CENTER COLUMBI	US	SIZE A	REVISION L	EVEL	5962-87571		
	OHIO 43218-3990				G	3		

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883	-	Test Method Standard Microcircuits.
MIL-STD-1835	-	Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings. MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <u>http://assist.daps.dla.mil/quicksearch/</u> or <u>http://assist.daps.dla.mil</u> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein and figures 1 and 2.

3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 3.

3.2.3 Radiation exposure circuit. The radiation exposure circuit shall be as specified on figure 4.

3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87571
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	T.	ABLE I. Electrical per	formance	characte	eristics	<u>.</u>			
Test	Symbol	$\begin{array}{c} \mbox{Conditions } \underline{1}/\\ -55^{\circ}C \leq T_A \leq +12\\ V_S = +5 \ V\\ \mbox{unless otherwise spectrum} \end{array}$	5°C	Group subgrou		Device type	Li	mits	Unit
							Min	Max	
Ambient error	E	Nominal output curre 298.15 μA at +25°C	ent is	1		All		5.0	±°C
				12		01		5.0	
				12		02		2.5	
				12		03		1.0	
				12		04		0.5	
		M,D,	P,L,R	12		03, 04	-10.0	1.0	
Absolute error	E _A	-55°C to +150°C wit external calibration		2, 3		01		10	
		-55°C to +125°C wit external calibration		2, 3	;	02		5.5	
				2, 3	5	03		3	
				2, 3		04		1.7	
Calibrated absolute error	Ec	-55°C to +150°C with ambient error (E) se zero. <u>3</u> / <u>4</u> /		2, 3	5	01		3	
		-55°C to +125°C wit external calibration.		2, 3	5	02		2	
			2, 3	5	03		1.6		
				2, 3		04		1	
Nonlinearity	NL	-55°C to +150°C 3/	<u>4/ 5</u> /	2, 3		01		1.5	
		-55°C to +125°C wit external calibration. $\underline{3}/\underline{4}$	hout <u>1</u> / <u>5</u> /	2, 3		02		0.8	
				2, 3	6	03		0.4	
				2, 3	5	04		0.3	
Repeatability	RPT	Max deviation betwee +25°C readings afte temperature. Cyclin between -55°C and +150°C. <u>3/ 5/ 6</u> /	r	1, 2,	3	All		0.1	
Long-term drift	ΔΕ/ΔΤ	Constant +5 V; Cons +125°C <u>3/</u> 5/	stant			All		0.1	±°C/ month
See footnotes at end of table	· ·								
STAN MICROCIRC	NDARD UIT DRAV	VING	SIZ J	ZE A				596	2-87571
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990					REVIS	SION LEVE G	EL	SHEET	5

	TABLE	I. Electrical performance chara	acteristics – Co	ntinued.			
Test	Symbol	$\begin{array}{c} \mbox{Conditions} \ \underline{1}/\ \underline{2}/ \\ -55^\circ C \leq T_A \leq +125^\circ C \\ V_S = +5 \ V \\ \mbox{unless otherwise specified} \end{array}$	Group A subgroups	Device type	Li	mits	Unit
					Min	Max	-
Power supply rejection ratio	PSRR	+4 V \leq V _S \leq +5 V $\underline{3}/\underline{5}/$	1	All		1	°C/V
		$+5 \text{ V} \le \text{V}_{\text{S}} \le +15 \text{ V} \underline{3}/ \underline{5}/$				0.4	-
		$+15 \text{ V} \le \text{V}_{\text{S}} \le +30 \text{ V} \underline{3}/ \underline{5}/$				0.2	-
Power supply voltage range	Vs	<u>3/</u> <u>5</u> /	1	All	+4		V
						+30	

1/ Device supplied to this drawing have been characterized through all levels M, D, P, L, R of irradiation. However, this device is only tested at the "R" level. Pre and Post irradiation values are identical unless otherwise specified in Table I.

2/ These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. Radiation end point limits for the noted parameters are guaranteed only for the conditions specified in MIL-STD-883, method 1019, condition A.

3/ This parameter is not tested post-irradiation.

 $\underline{4}$ / See figure 5.

5/ Guaranteed if not tested.

 $\underline{6}$ / For device types 02, 03, and 04 class V maximum temperature = +125°C.

3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 <u>Notification of change for device class M</u>. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.

3.9 <u>Verification and review for device class M</u>. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

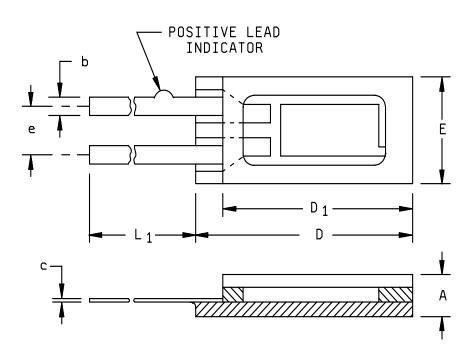
3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 59 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

STANDARD	SIZE		
MICROCIRCUIT DRAWING	Α		5962-87571
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Symbol	Inc	hes	Millim	Notes	
	Min	Max	Min	Max	
А	0.041	0.050	1.04	1.27	
b	0.015	0.019	0.38	0.48	
с	0.0045	0.0065	0.12	0.17	
D		0.250		6.35	2
D ₁		0.220		5.59	
E	0.081	0.093	2.06	2.36	2
е	0.045	0.056	1.14	1.40	
L ₁	0.500		12.69		

NOTES:

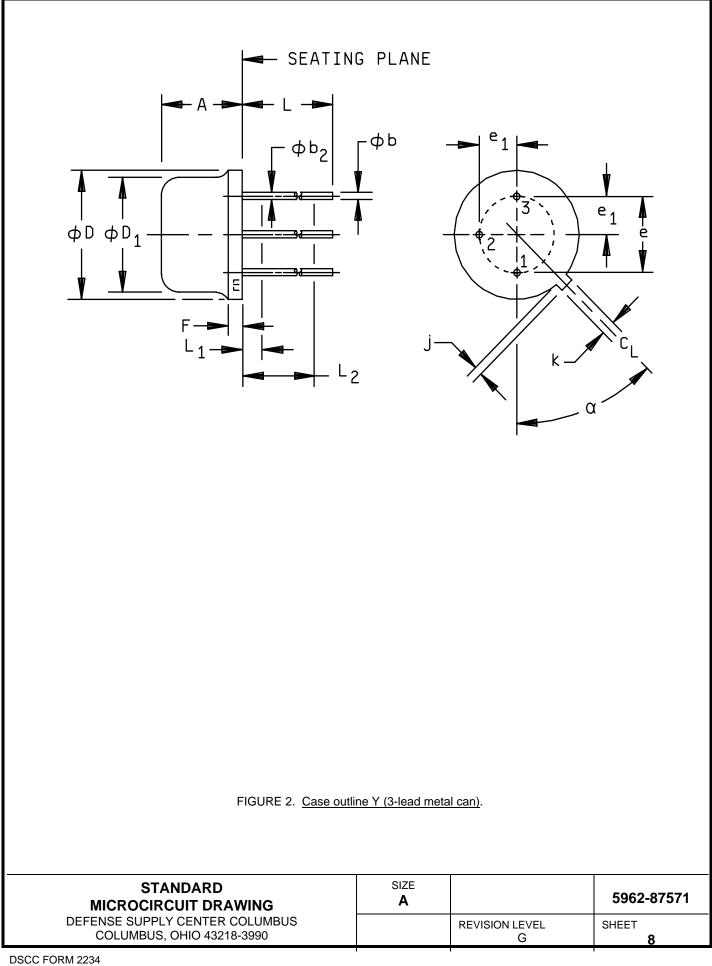
1. The US government preferred system of measurement is the metric SI system. However, this item was originally designed using inch-pound units of measurement. In the event of conflict between the metric and inch-pound units, the inch-pound units shall take precedence.

2. This dimension allows for off-center lid, meniscus and solder overrun.

3. Top view.

FIGURE 1. Case outline X (2-lead, 0.087" x 0.250" flat package).

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87571
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990		REVISION LEVEL G	SHEET 7



Symbol	Incl	hes	Millim	neters	Notes
	Min	Max	Min	Max	
А	0.115	0.150	2.92	3.81	
φb		0.021		0.53	2, 5
φb2	0.016	0.019	0.41	0.48	2, 5
φD	0.209	0.230	5.31	5.84	
φD ₁	0.178	0.195	4.52	4.95	
е	0.100	BSC	2.54	BSC	3
e ₁	0.050	BSC	1.27	BSC	3
F		0.030		0.76	
j	0.036	0.046	0.91	1.17	
k	0.028	0.048	0.71	1.22	4
L	0.500		12.70		2
L ₁		0.050		1.27	2
L ₂	0.250		6.35		
α	45°	BSC	45°	BSC	

NOTES:

- 1. The US government preferred system of measurement is the metric SI system. However, this item was originally designed using inch-pound units of measurement. In the event of conflict between the metric and inch-pound units, the inch-pound units shall take precedence.
- 2. (Three leads) ϕb_2 applies between L₁ and L₂. ϕb applies between L₂ and 0.5 inch (12.70 mm) from seating plane. Diameter is uncontrolled in L₁ and beyond 0.5 inch (12.70 mm) from seating plane.
- 3. Leads having maximum diameter 0.019 inch (0.48 mm) measured in gauging plane 0.054 inch (1.4 mm) + 0.001 inch (0.03 mm) 0.000 inch (0.00 mm) below the seating plane of the device are within 0.007 inch (0.18 mm) of their true positions relative to a maximum-width tab.
- 4. Measured from maximum diameter of the actual device.
- 5. All leads: Increase maximum limit by 0.003 inch (0.08 mm) when hot solder dip finish is applied.

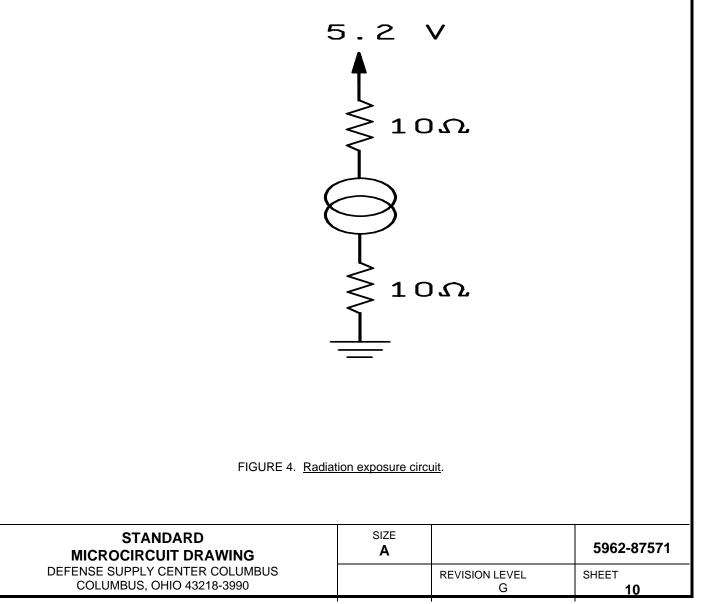
FIGURE 2. Case outline Y (3-lead metal can) - Continued.

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Device types	01-04	01-04
Case outlines	х	Y
Terminal number	Termi	nal symbol
1	+	+
2	-	-
3		NC

NC = No connect





NOTE: V_s across device must remain constant or PSRR error	1590 $V_T = 1$ -0 - r must be included	d.	
STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS	SIZE A	REVISION LEVEL	5962-87571

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgr (in accord: MIL-PRF-385	ance with
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)			
Final electrical parameters (see 4.2)	1, 2, 3, 12 <u>1</u> /	1, 2, 3, 12 <u>1</u> /	1, 2, 3, 12 <u>1</u> / <u>2</u> /
Group A test requirements (see 4.4)	1, 2, 3, 12	1, 2, 3, 12	1, 2, 3, 12
Group C end-point electrical parameters (see 4.4)	1	1	1 <u>2</u> /
Group D end-point electrical parameters (see 4.4)	1	1	1
Group E end-point electrical parameters (see 4.4)			1

TABLE IIA. Electrical test requirements.

 <u>1</u>/ PDA applies to subgroup 1. Delta's excluded from PDA.
 <u>2</u>/ Delta limits in accordance with table IIB shall be computed with reference to the previous interim electrical parameters.

TABLE IIB. 240 hour burn-in and group C end-point electrical parame

Parameter	Device	Burn-in	Burn-in	Group C	Group C	Units
	types	endpoint	delta	endpoint	delta	
Ambient error	02	2.5	0.5	3.5	1.0	±°C
(E)	03	1.0	0.5	2.0	1.0	±°C
	04	0.5	0.5	1.5	1.0	±°C

4.2.1 Additional criteria for device class M.

- a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.

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4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 4, 5, 6, 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.
- c. Optional subgroup 12 is used for grading and part selection at +25°C, it is not included in PDA.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

- 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - b. $T_A = +125^{\circ}C$, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

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MICROCIRCUIT DRAWING	A		5962-87571
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4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table IIA herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.

4.4.4.1 <u>Total dose irradiation testing</u>. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A and as specified herein.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractorprepared specification or drawing.

6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 <u>Record of users</u>. Military and industrial users should inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.

6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.

6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87571
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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 07-05-14

Approved sources of supply for SMD 5962-87571 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DSCC maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-8757101XA	24355 (2)	AD590JF/883B
5962-8757101YA	24355 (2)	AD590JH/883B
5962-8757102XA	24355 (2)	AD590KF/883B
5962-8757102YA	24355 (2)	AD590KH/883B
5962-8757102VXA	<u>3</u> /	AD590KF/QMLV
5962-8757102VYA	<u>3</u> /	AD590KH/QMLV
5962-8757103XA	24355 (2)	AD590LF/883B
5962-8757103YA	24355 (2)	AD590LH/883B
5962-8757103VXA	24355 (4)	AD590LF/QMLV
5962-8757103VYA	24355 (4)	AD590LH/QMLV
5962R8757103VXA	24355 (4)	AD590LF/QMLR
5962R8757103VYA	24355 (4)	AD590LH/QMLR
5962-8757104XA	24355 (2)	AD590MF/883B

See footnotes at end of table.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-8757104YA	24355 (2)	AD590MH/883B
5962-8757104VXA	24355 (4)	AD590MF/QMLV
5962-8757104VYA	24355 (4)	AD590MH/QMLV
5962R8757104VXA	24355 (4)	AD590MF/QMLR
5962R8757104VYA	24355 (4)	AD590MH/QMLR

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- <u>2</u>/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- 3/ Not available from an approved source of supply.

Vendor CAGE number	Vendor name and address
24355	Analog Devices (2) RT 1 Industrial Park PO Box 9106 Norwood, MA 02062 Point of contact: 804 Woburn Street Wilmington, MA 01887-3462
24355	Analog Devices (4) RT 1 Industrial Park PO Box 9106 Norwood, MA 02062 Point of contact: 7910 Triad Center Drive Greensboro, NC 27409-9605

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.